Coulomb Interaction-Stabilized Chern Insulators with C > 1 in Twisted Rhombohedral Trilayer-Bilayer Graphene



arXiv:2505.07981

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100 Years of Quantum Physics Quy Nhơn, Việt Nam



Prof. Cyprian Lewandowski

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Quantum Hall Insulators

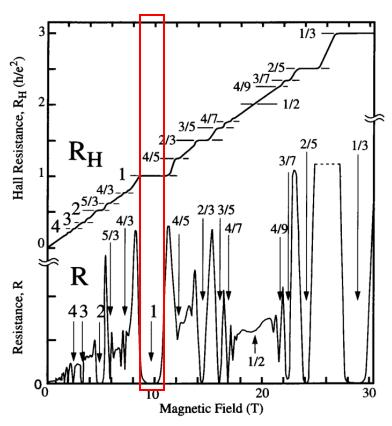
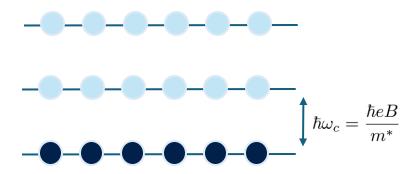


Figure 18. The FQHE as it appears today in ultra-high mobility modulation doped GaAs / AlGaAs 2DESs. Many fractions are visible. The most prominent sequence, $v=p/(2p\pm1)$, converges toward v=1/2 and is discussed in the text.

Stormer, Horst L. "Nobel lecture: the fractional quantum Hall effect." *Reviews of Modern Physics* 71.4 (1999): 875.



- Integer quantum Hall effect =
 full Landau levels filled
 - Used as resistance standard

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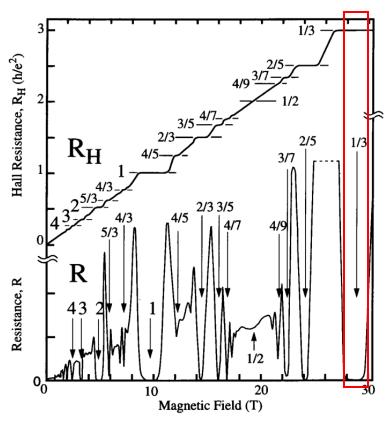
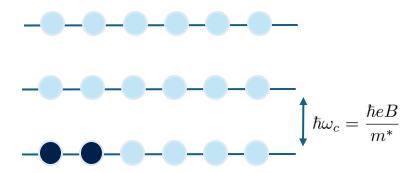


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- Integer quantum Hall effect =
 full Landau levels filled
 - Used as resistance standard
- Fractional quantum Hall effect
 = partial Landau levels filled
 - Host Abelian and non-Abelian anyons potentially useful for topological quantum computation

Why is quantization of the Hall conductivity so precise?

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• By imposing a lattice, Thouless, Kohmoto, Nightingale, and den Nijs gave an explicit formula to compute the Hall conductivity

Chern number
$$\mathcal{C} = \frac{1}{2\pi} \int d^2 \mathbf{k} \mathcal{B}_z(\mathbf{k})$$
 Berry curvature
$$\mathcal{B}_z(\mathbf{k}) = -i\nabla \times \langle u_\mathbf{k} | \nabla_\mathbf{k} | u_\mathbf{k} \rangle$$

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- Berry curvature is like a built-in magnetic field
- Its integral over a Brillouin zone is always an integer a topological number!
- Each Landau level has a Chern number of one

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The Chern number is defined for any lattice system, completely agnostic of the origin of timereversal symmetry breaking!

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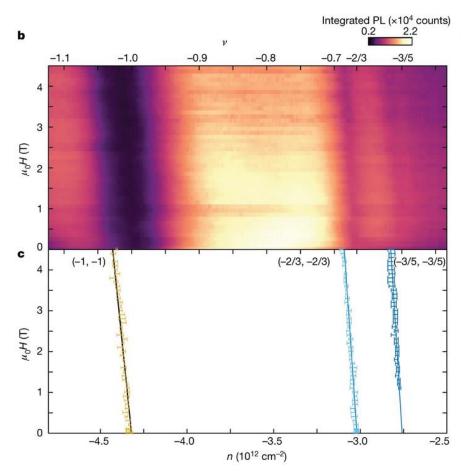
No magnetic field needed – lifting a major technical hurdle

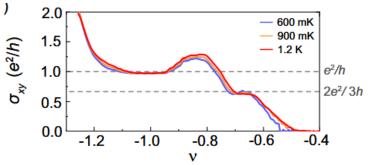
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Partially-filled Chern number ≠ 0 bands sometimes form fractional Chern insulators – featuring quantized Hall conductivity and may host anyonic statistics

No magnetic field needed – lifting a major technical hurdle

This has been seen in two different classes of materials





Twisted MoTe2

• Fractions seen: 1, 2/3, 3/5

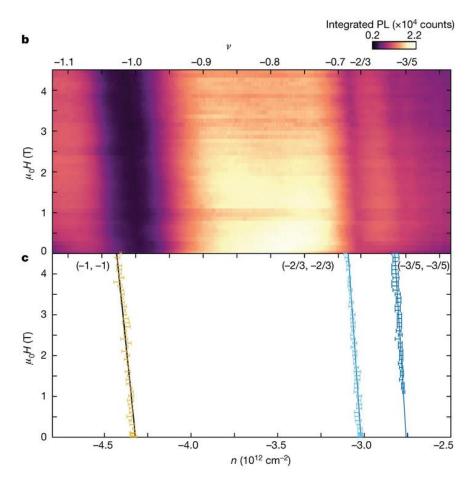
Cai, Jiaqi, et al. *Nature* 622.7981 (2023): 63-68. Zeng, Yihang, et al. *Nature* 622.7981 (2023): 69-73. Redekop, Evgeny, et al. *Nature* 635.8039 (2024): 584-589. Xu, Fan, et al. *Physical Review X* 13.3 (2023): 031037.

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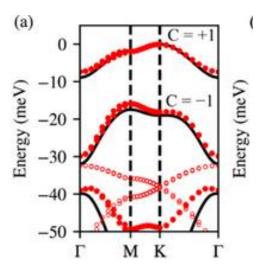


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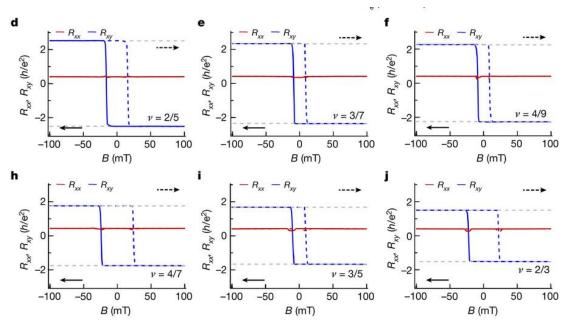
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Wang, Chong, et al. *Phys. Rev. Lett.* 132.3 (2024): 036501. Reddy, Aidan P., et al. *Phys. Rev. B* 108.8 (2023): 085117. Yu, Jiabin, et al. *Phys. Rev. B* 109.4 (2024): 045147. Jia, Yujin, et al. *Phys. Rev. B* 109.20 (2024): 205121.

Twisted MoTe2

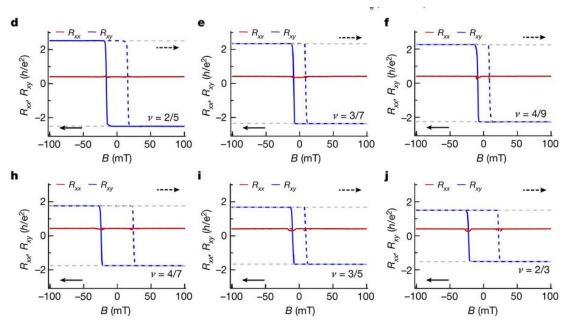
- Fractions seen: 1, 2/3, 3/5
- Noninteracting band structure contains narrow, isolated Chern bands.
- Chern number = 1



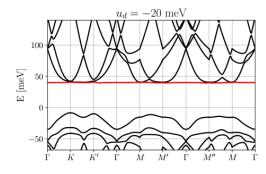
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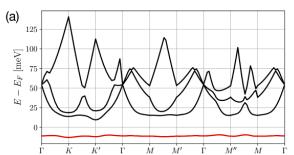
Multilayer Graphene/hBN

- Fractions seen: 1, 2/3, 3/5, 4/7, 4/9, 3/7, 2/5, 5/9, 5/11
- Number of layers: 4, 5, 6
- At large displacement field



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Multilayer Graphene/hBN

- Fractions seen: 1, 2/3, 3/5, 4/7, 4/9, 3/7, 2/5, 5/9, 5/11
- Number of layers: 4, 5, 6
- At large displacement field
- Noninteracting band structure contains narrow, but **not** isolated, Berry-curvature rich bands
- Chern number = 1
- Role of substrate is unclear

Dong, Zhihuan, Adarsh S. Patri, and Todadri Senthil. *Phys. Rev. Lett.* 133.20 (2024): 206502.

Herzog-Arbeitman, Jonah, et al. *Phys. Rev. B* 109.20 (2024): 205122.

Dong, Junkai, et al. *Phys. Rev. Lett.* 133.20 (2024): 206503. Kudo, Koji, Ryota Nakai, and Kentaro Nomura. *Phys. Rev. B* 110.24 (2024): 245135.

Guo, Zhongqing, et al. *Phys. Rev. B* 110.7 (2024): 075109. Zhou, Boran, Hui Yang, and Ya-Hui Zhang. *Phys. Rev. Lett.* 133.20 (2024): 206504.

Huang, Ke, et al. Phys. Rev. B 110.11 (2024): 115146.

Motivation

Now that FCI's from C = 1 bands have been experimentally observed, we are motivated to search for

lattice systems that host bands which are:

- Narrow and isolated post-Hartree Fock renormalization
- Topological with Chern numbers > 1 beyond Landau level paradigm
- Possible candidates for FCI's upon doping

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Analogy to the zeroth Landau level: Trace condition violation

Quantum metric
$$g_{\mu\nu}(\mathbf{k}) = \frac{\langle \partial_{\mu} u_{\mathbf{k}} | \partial_{\nu} u_{\mathbf{k}} \rangle + \langle \partial_{\nu} u_{\mathbf{k}} | \partial_{\mu} u_{\mathbf{k}} \rangle}{2} - \langle \partial_{\mu} u_{\mathbf{k}} | u_{\mathbf{k}} \rangle \langle u_{\mathbf{k}} | \partial_{\nu} u_{\mathbf{k}} \rangle$$

The quantum metric measures distances between Bloch states.

$$\lambda = \frac{1}{2\pi} \int d^2 \mathbf{k} \left[\text{Tr} g_{\mu\nu}(\mathbf{k}) - |\mathcal{B}_z(\mathbf{k})| \right]$$

This quantity is exactly **zero** for the **zeroth** Landau level, is **two** for the **first** Landau level, and is **four** for the **second** Landau level.

Ledwith, Patrick J., et al. Phys. Rev. Res. 2.2 (2020): 023237.

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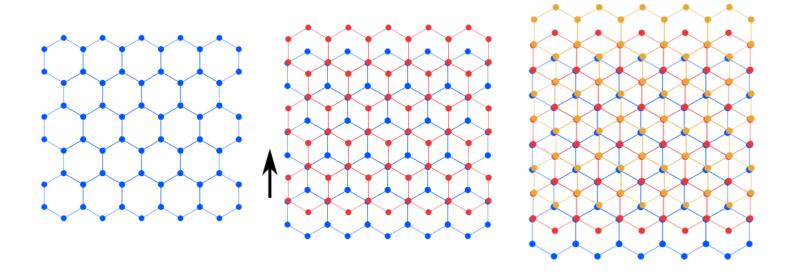
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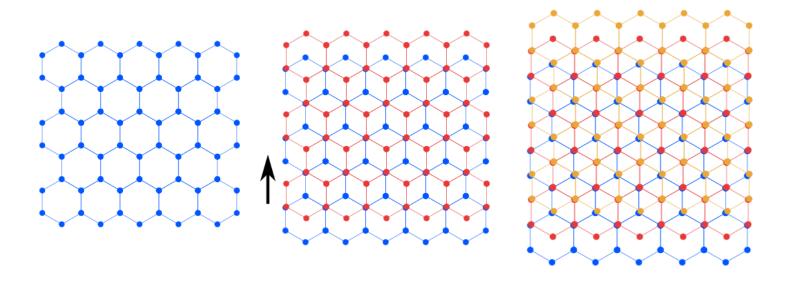
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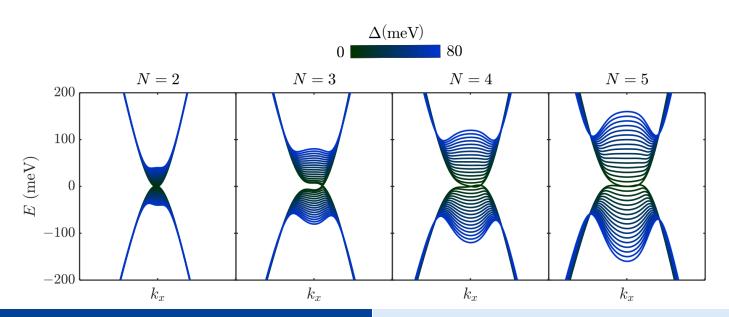
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Rhombohedral Graphene Multilayer

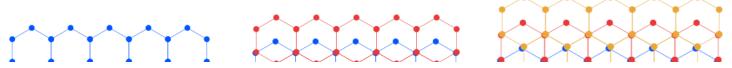


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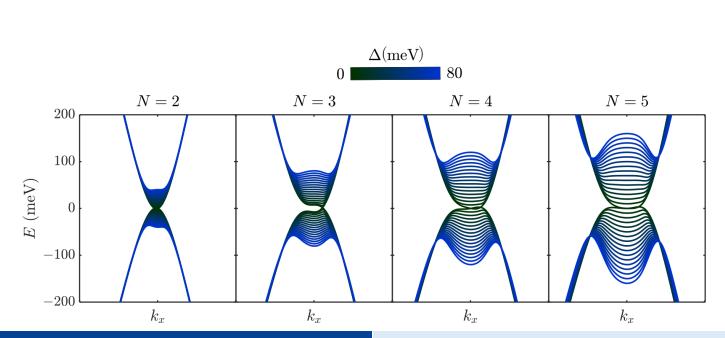




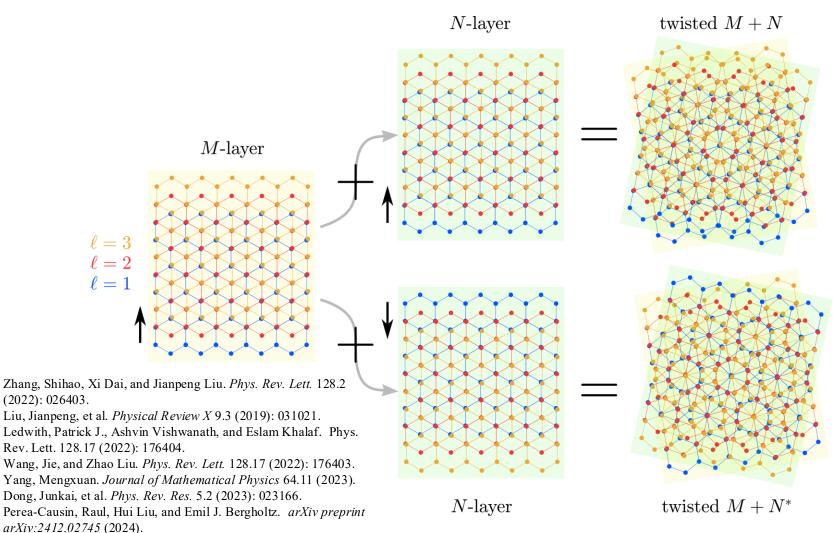
Rhombohedral Graphene Multilayer



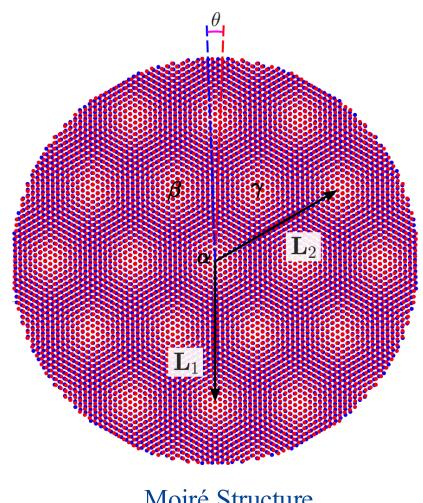
- Band structures can be gapped by interlayer displacement field
- Bottom of conduction band flattens with increasing field
- The more layers, the smaller the field needed to achieve the same gap



Parallel Configuration



Antiparallel Configuration



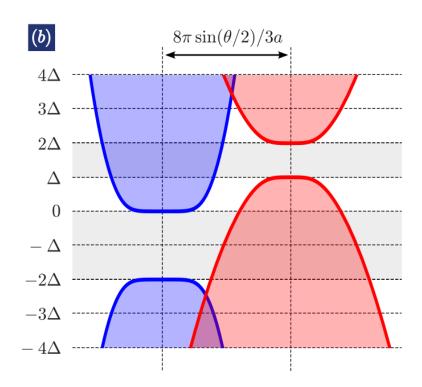
Moiré Structure



For concreteness, we consider twisted 3+2 multilayer graphene for the remainder of this talk.

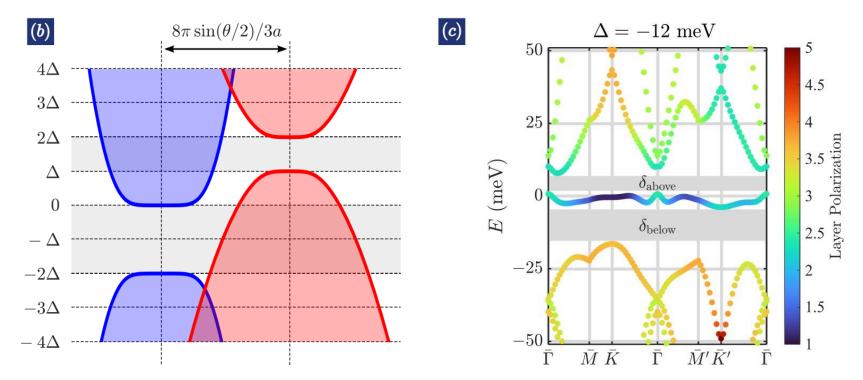
Twisted 3+2 Multilayer Graphene





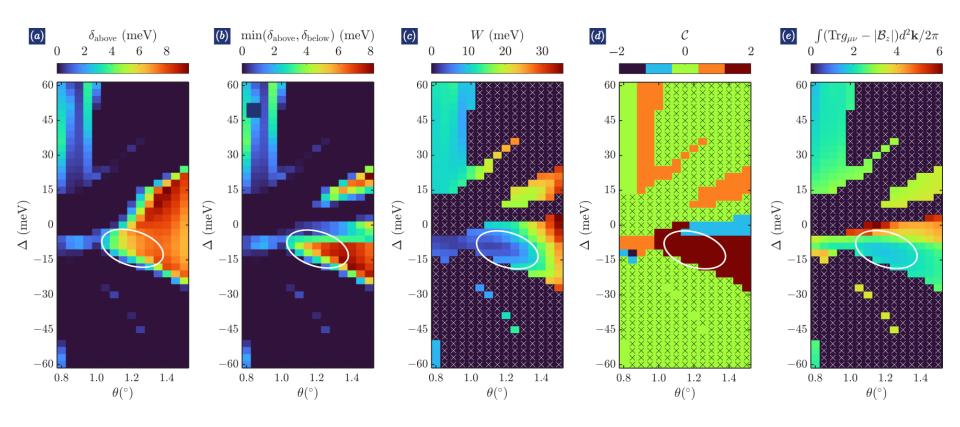




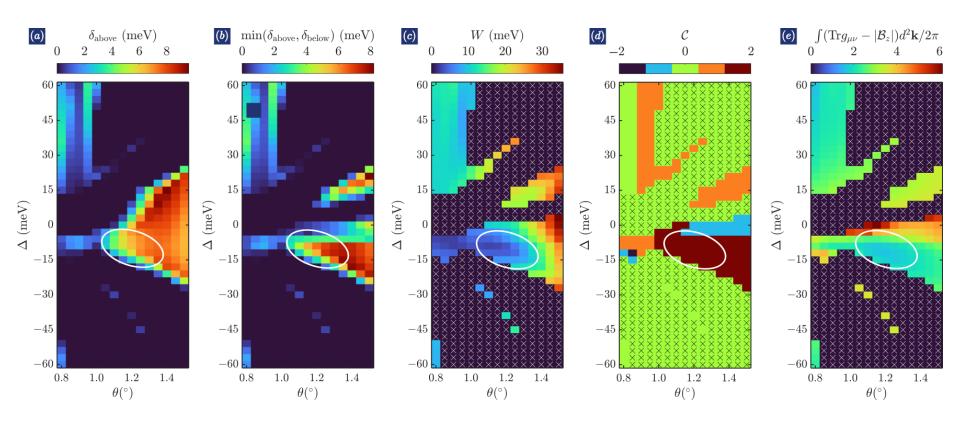


Hybridization is crucial for gap formation, i.e. moiré structure is important!

Antiparallel Stacking Order



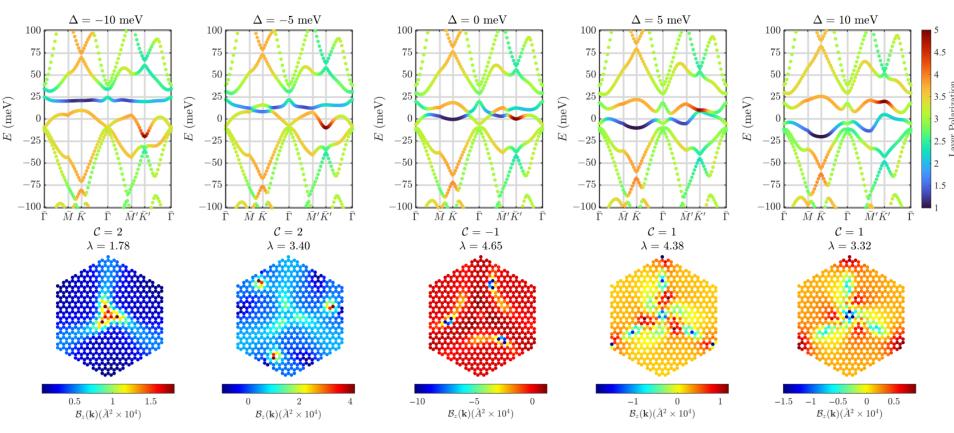
Antiparallel Stacking Order



There exists a region in phase space which simultaneously has:

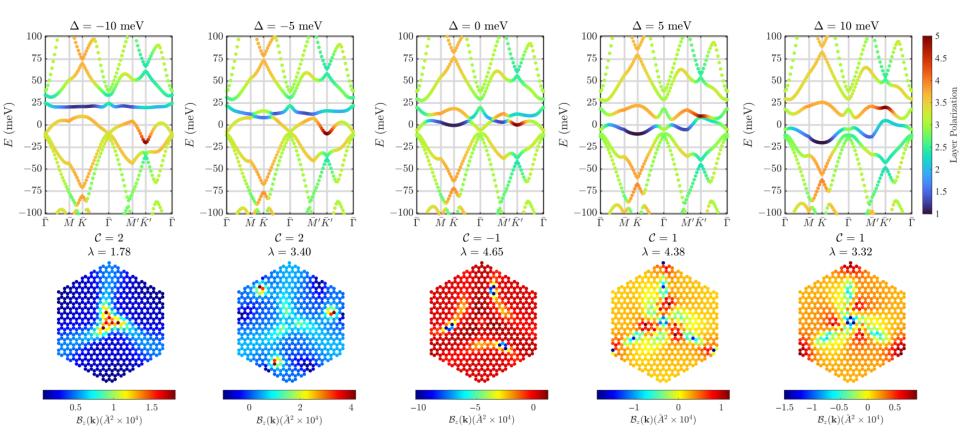
(1) large gaps, (2) small bandwidths, (3) Chern number = 2, and (4) the trace condition is relatively small ~ 1.7

Antiparallel Stacking Order



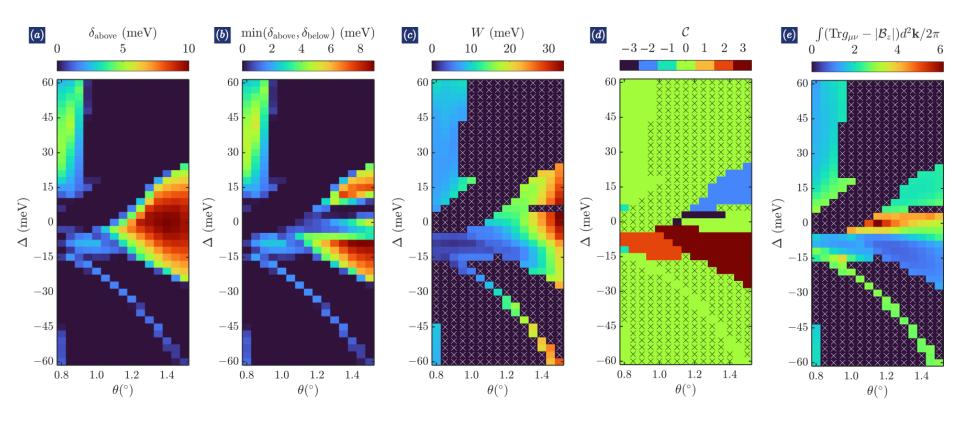
• As Δ increases in the **negative** direction, a Chern-two band flattens. Charge density is localized on the trilayer substack.

Antiparallel Stacking Order

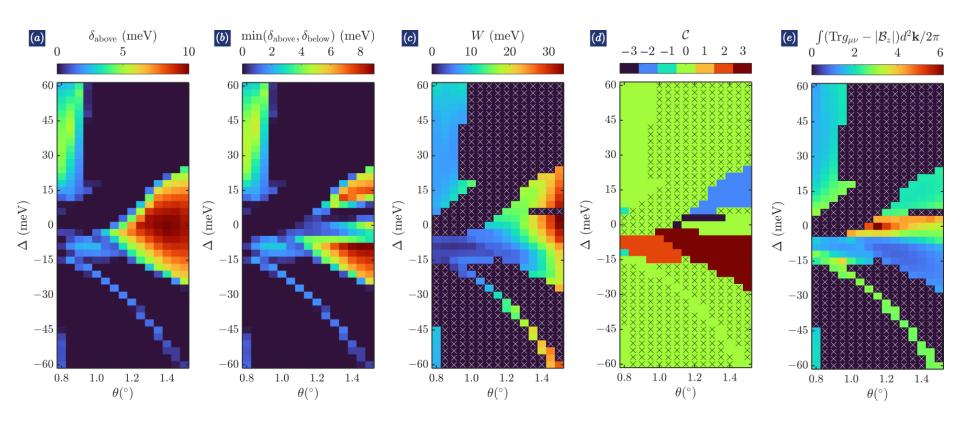


- As Δ increases in the **negative** direction, a Chern-two band flattens. Charge density is localized on the trilayer substack.
- As Δ increases in the **positive** direction, a Chern-one band develops but is not isolated. Charge density is localized on the bilayer substack.

Parallel Stacking Order



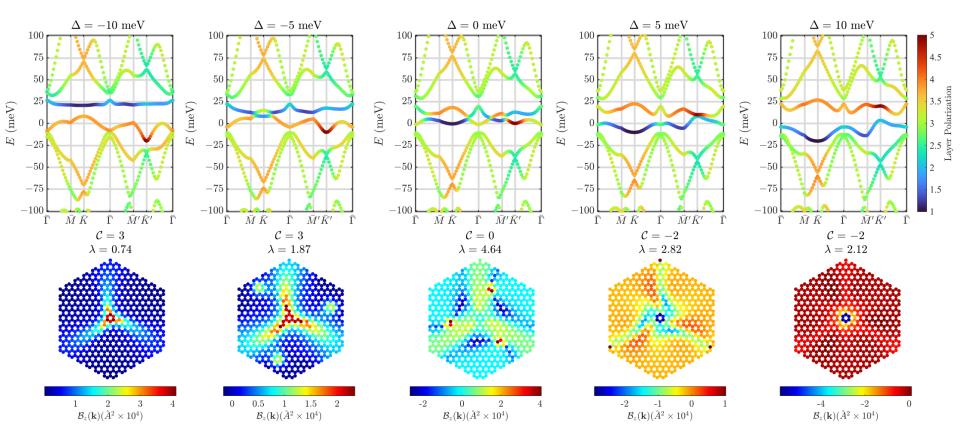
Parallel Stacking Order



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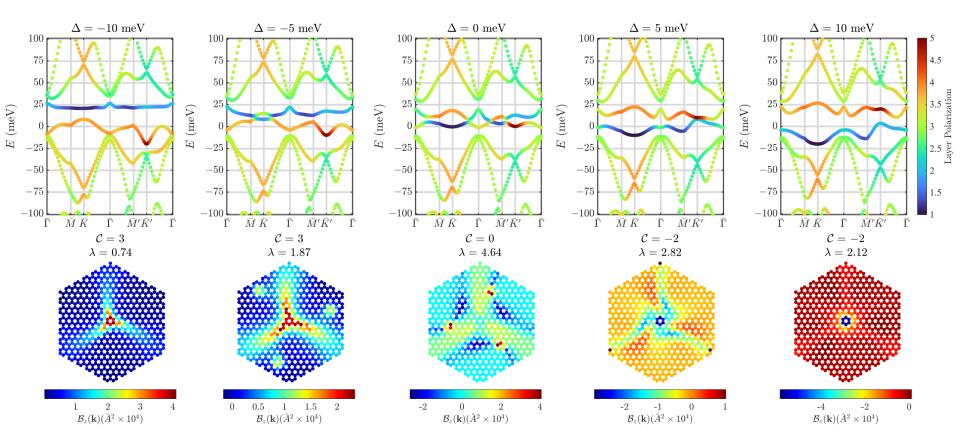
(1) large gaps, (2) small bandwidths, (3) Chern number = 3, and (4) the trace condition is quite small ~ 0.74

Parallel Stacking Order



• As Δ increases in the **negative** direction, a Chern-three band flattens. Charge density is localized on the trilayer substack.

Parallel Stacking Order



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Self-Consistent Mean-Field Theory

$$\hat{\mathcal{H}} = \sum_{\substack{\mathbf{k} \in \text{mBZ} \\ n, n', \xi, \xi'}} \hat{\Psi}_{n, \xi, \mathbf{k}}^{\dagger} \left[\mathbb{K}_{\xi, \xi'}^{n, n'}(\mathbf{k}) + \mathbb{H}_{\xi, \xi'}^{n, n'}(\mathbf{k}) + \mathbb{F}_{\xi, \xi'}^{n, n'}(\mathbf{k}) \right] \hat{\Psi}_{n', \xi', \mathbf{k}},$$

$$\mathbb{K}_{\xi, \xi'}^{n, n'}(\mathbf{k}) = \delta_{\xi, \xi'} \delta_{n, n'} E_{n, \xi}(\mathbf{k}),$$

$$\mathbb{H}_{\xi, \xi'}^{n, n'}(\mathbf{k}) = +\delta_{\xi, \xi'} \sum_{\substack{\mathbf{p} \in \text{mBZ} \\ n_1, n_3, \xi_1}} \mathbb{V}_{\xi_1, \xi}^{n_1, n, n, n_3, n'}(\mathbf{p}, \mathbf{k}, \mathbf{0}) \mathbb{D}_{\xi_1, \xi_1}^{n_1, n_3}(\mathbf{p})$$

$$\mathbb{F}_{\xi, \xi'}^{n, n'}(\mathbf{k}) = -\sum_{\substack{\mathbf{p} \in \text{mBZ}}} \mathbb{V}_{\xi', \xi}^{n_1, n, n', n_4}(\mathbf{k}, \mathbf{p}, \mathbf{p} - \mathbf{k}) \mathbb{D}_{\xi', \xi}^{n_1, n_4}(\mathbf{p}).$$

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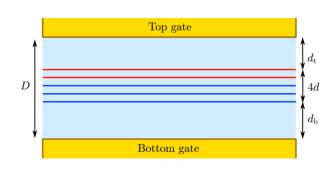
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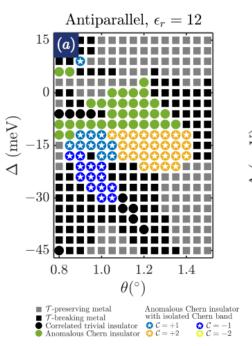
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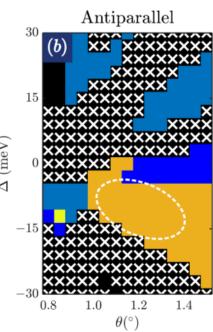
$$\mathcal{V}(\mathbf{k}, z, z') = \frac{e^2 \operatorname{csch}(kD)}{2\epsilon_0 \epsilon_r k} \left[\cosh(k \left[D - |z - z'| \right]) - \cosh(k \left[D - |z + z'| \right]) \right]$$

- Use layer-dependent Coulomb potential to account for uneven charge distribution
- Search for *T*-breaking isospin-polarized ground states

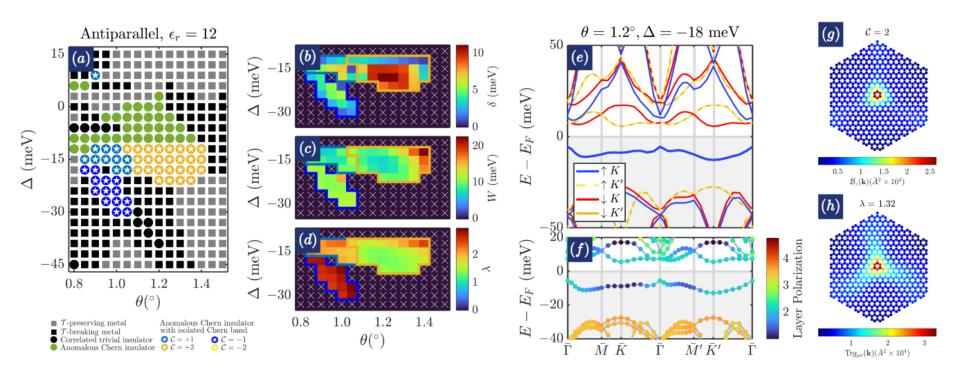


Antiparallel Stacking Order



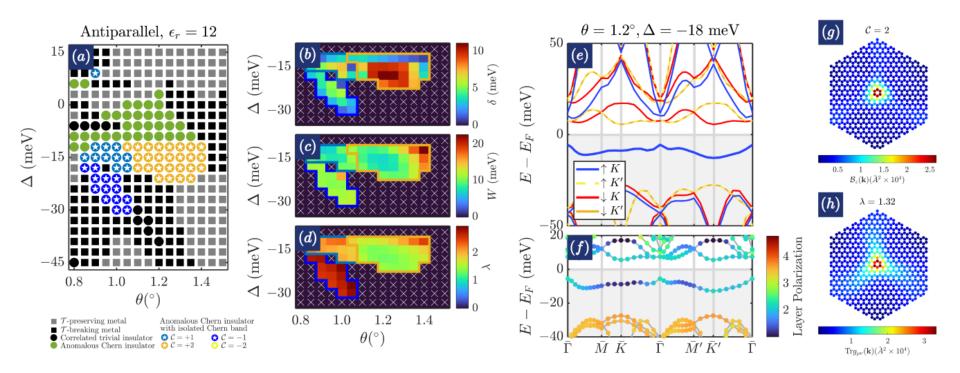


Antiparallel Stacking Order



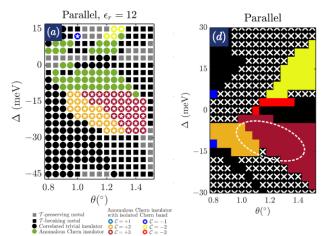
- The Chern-two phase is present even when interactions are included at the mean-field level
- Bands remain relatively narrow and well-isolated

Antiparallel Stacking Order

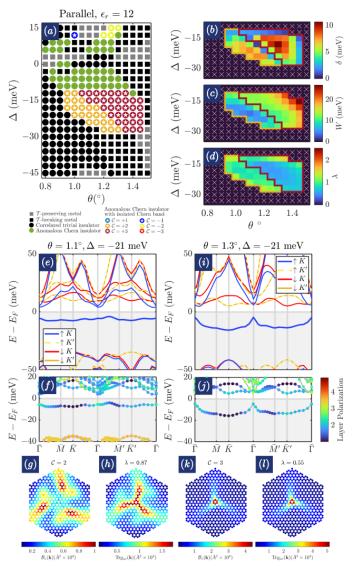


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- Bands remain relatively narrow and well-isolated
- The trace violation is reduced by interactions: $1.7 \rightarrow 1.4$

Parallel Stacking Order

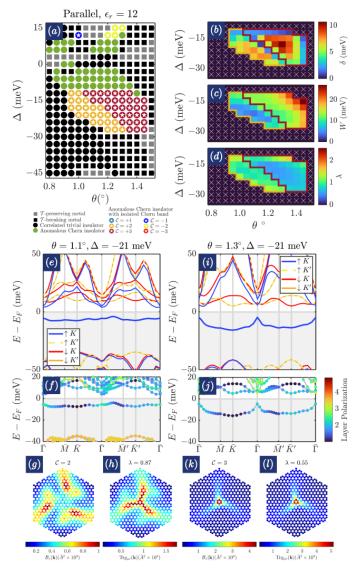


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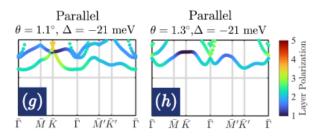


• The Chern-three phase is intertwined with the Chern-two phase when interactions are included at the mean-field level

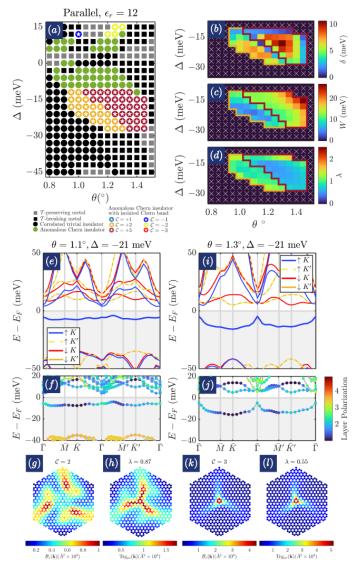
Parallel Stacking Order



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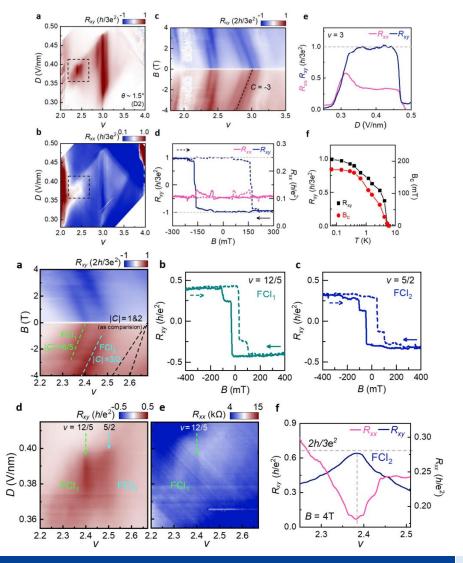
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- The Chern-two phase exists in a parameter regime where the noninteracting bands are not even isolated or topological
- The trace violation is reduced by interactions: $0.74 \rightarrow 0.5$

Trace condition for pentalayer: 0.6-1.45

Trace condition for MoTe2: 0.1-0.7

Experimental Confirmation

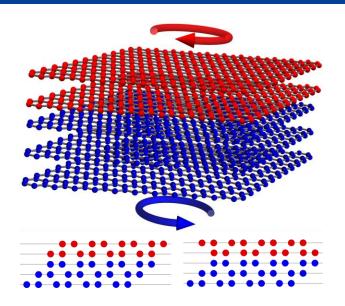
Dong, Jingwei, et al. "Observation of Integer and Fractional Chern insulators in high Chern number flatbands." *arXiv preprint arXiv:2507.09908* (2025).

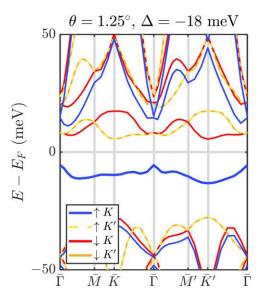


Transport experiment on twisted 3+2 rhombohedral graphene:

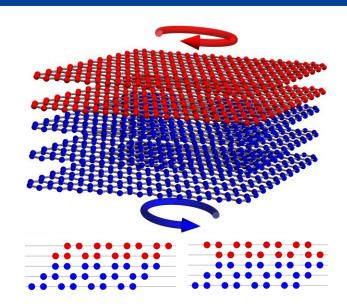
- Experimental evidence using Hall conductivity and Streda's slope
- Quantized C = 3 Chern insulator
- Fractional Chern insulators at $v \sim 12/5$ and $v \sim 5/2$
- Anomalous Hall crystals near $v \sim 1$

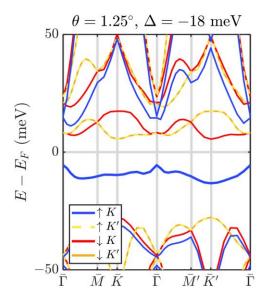
Twisted M + N multilayer graphene features narrow topological bands with C > 1.



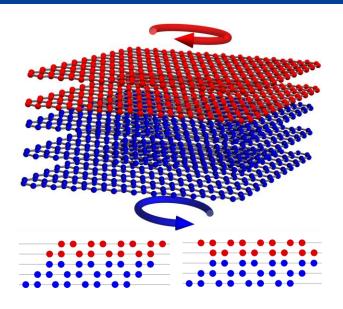


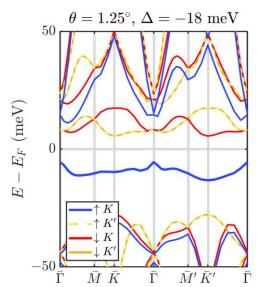
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- These bands are robust in mean-field calculations.



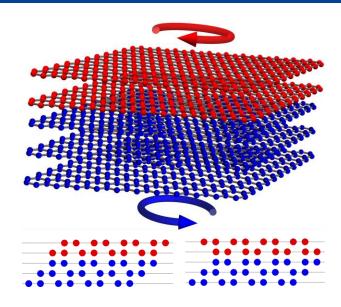


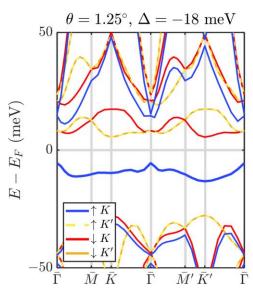
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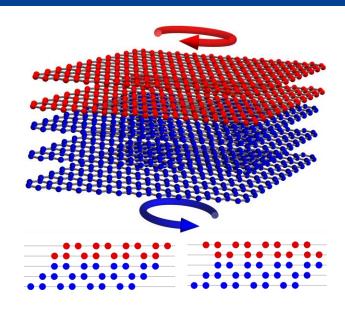
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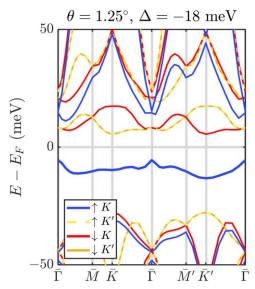


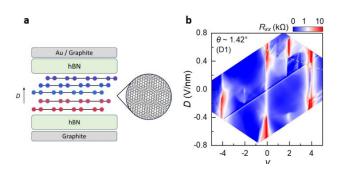


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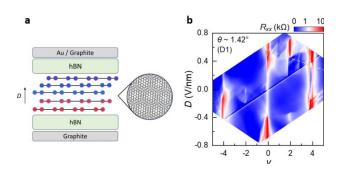
Thank you!





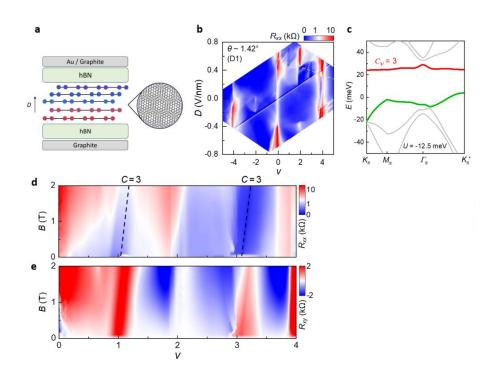


• D1 at $\theta = 1.42^{\circ}$ at T = 1 K

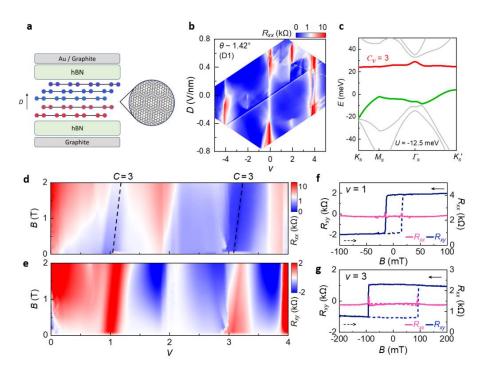


Positive D
pushes
electrons
to the
trilayer
side

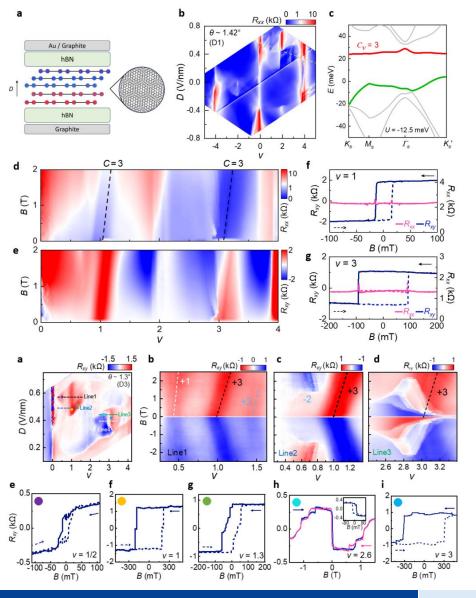
- D1 at $\theta = 1.42^{\circ}$ at T = 1 K
- Correlated insulators for v = 1, 2, and 3 at positive D



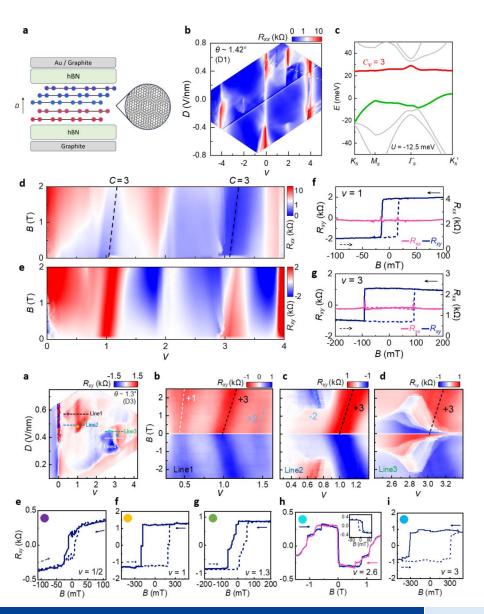
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- Correlated insulators for v = 1, 2, and 3 at positive D
- v = 1 with D = 0.517 V/nm according to Streda's formula but no quantized Hall conductivity.
- v = 3 with D = 0.376
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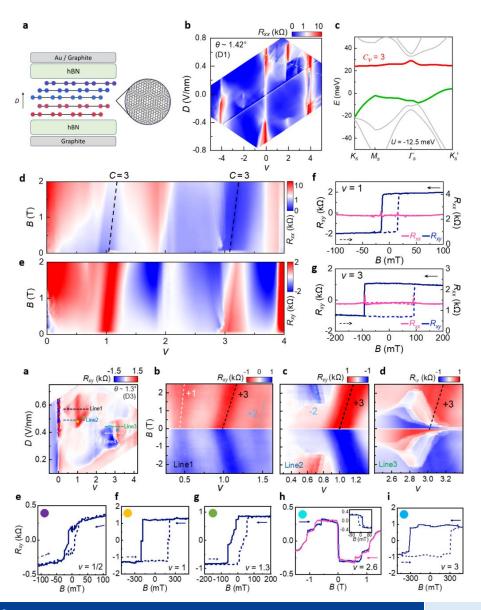
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- D3 at $\theta = 1.30^{\circ}$ at B = 0.5 T and T = 1.1 K

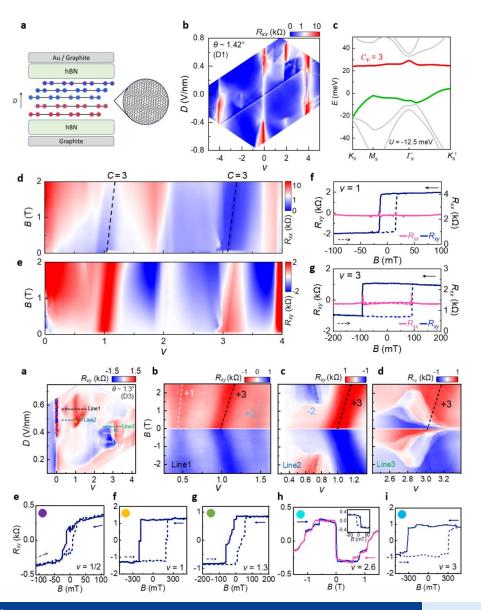


Why no quantization of Hall conductivity?



Why no quantization of Hall conductivity?

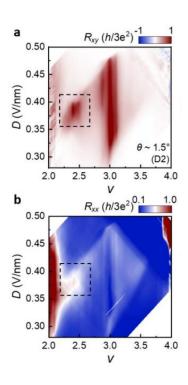
 Degradation due to cooling down? Second cooling down has worse quantization



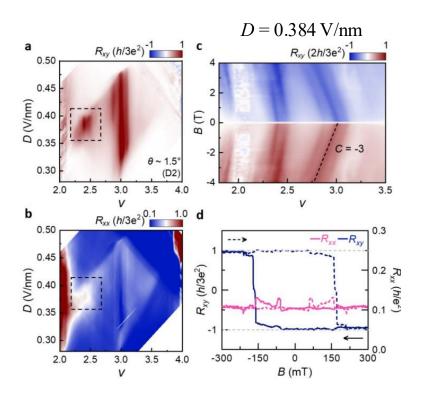
Why no quantization of Hall conductivity?

- Degradation due to cooling down? Second cooling down has worse quantization
- Thermal absorption due to evaporated metal particles?
 Changing gates can help

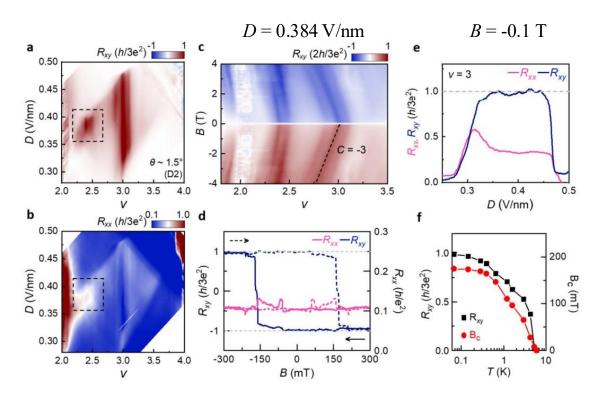
• D2 contains thin graphite gates at $\theta = 1.50^{\circ}$



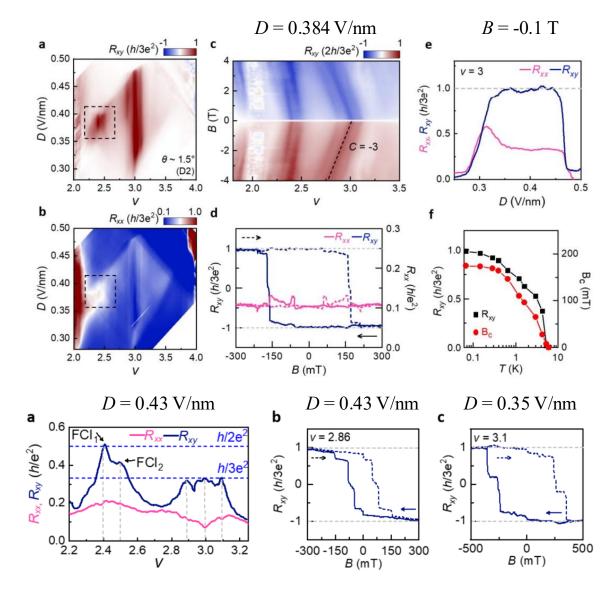
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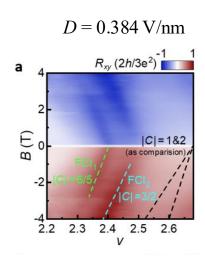
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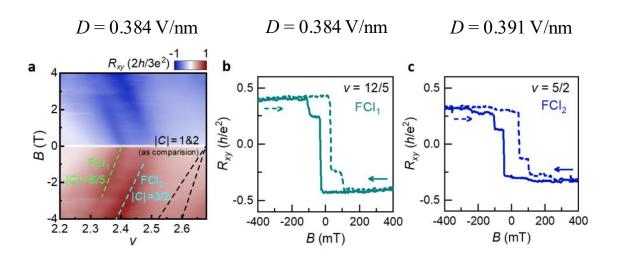
- D2 contains thin graphite gates at $\theta = 1.50^{\circ}$
- Quantized Hall conductivity with accuracy > 98.2%
- Topological states at incommensurate fillings v = 2.86 and 3.1?
 Anomalous Hall crystal?



• FC1

- $\circ v \sim 12/5 (v*\sim 2/5)$
- \circ C = 6/5 odd denominator

- FC2
 - \circ $v \sim 5/2 (v* \sim 1/2)$
 - o C = 3/2 even denominator

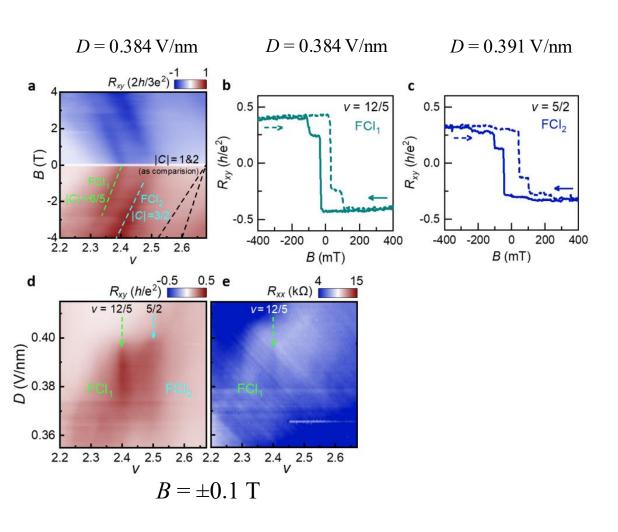


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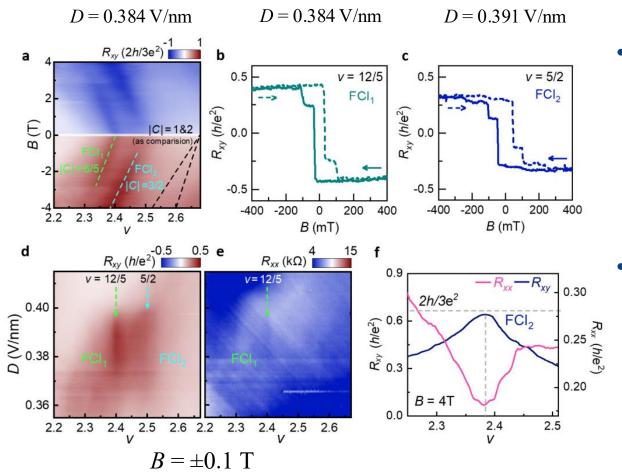


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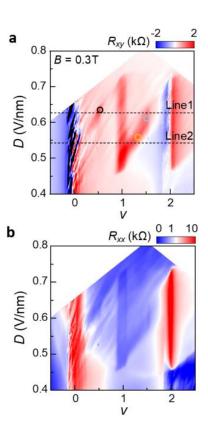


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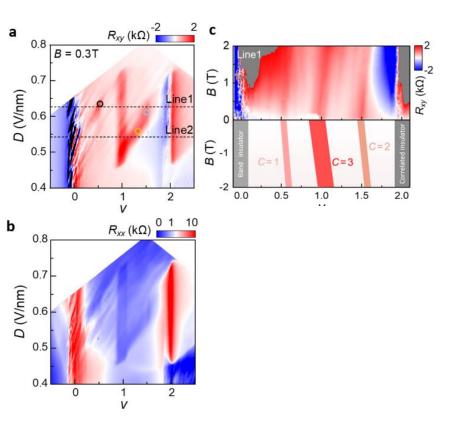
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FC2

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- o C = 3/2 even denominator
- Can be stablized by a magnetic field of 4 T



• Integer Chern insulators at fractional fillings



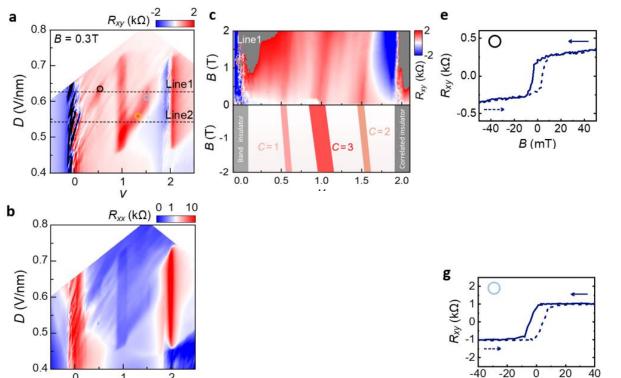
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$$v = 1/2 \text{ with } C = 1$$

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• Again, no quantization

B (mT)



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- Time reversal symmetry breaking

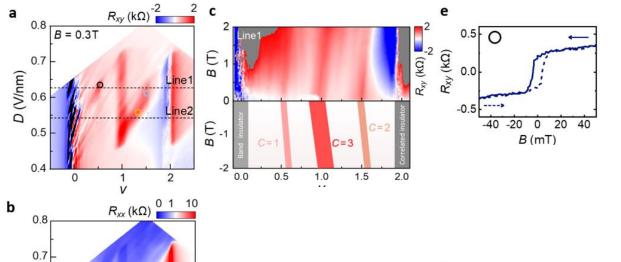
g

 R_{xy} (k Ω)

20

B (mT)

-20



• Integer Chern insulators at fractional fillings

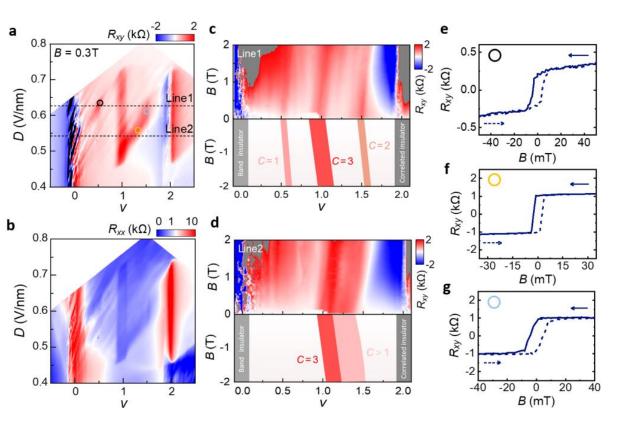
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- Some sort of competing order between charge and topology?

D (V/nm)

0.5



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- Extended Hall crystal phase?

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